

## Silicon PNP Power Transistors

2SA1941

## DESCRIPTION

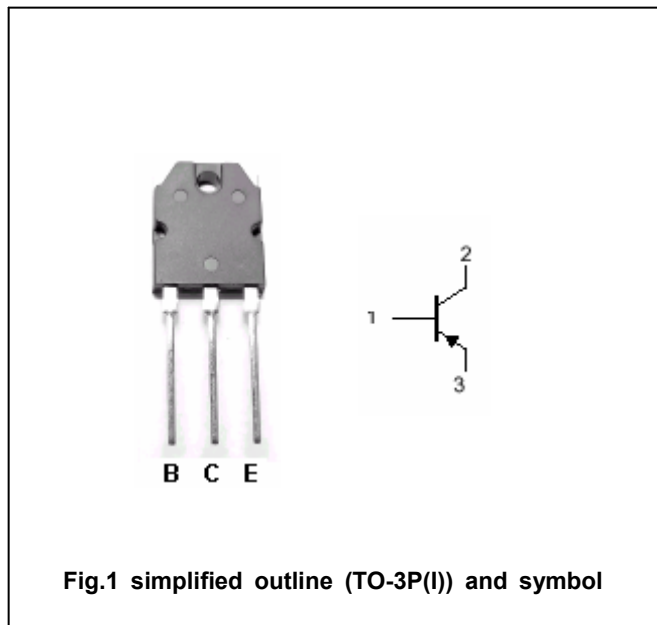
- With TO-3P(I) package
- Complement to type 2SC5198

## APPLICATIONS

- Power amplifier applications
- Recommend for 70W high fidelity audio frequency amplifier output stage

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_c=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-140	V
$V_{CEO}$	Collector-emitter voltage	Open base	-140	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-10	A
$I_B$	Base current		-1	A
$P_C$	Collector power dissipation	$T_c=25^\circ\text{C}$	100	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-55~150	$^\circ\text{C}$

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=-50mA; I_B=0$	-140			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=-7A; I_B=-0.7A$			-2.0	V
$V_{BE}$	Base-emitter voltage	$I_C=-5A; V_{CE}=-5V$			-1.5	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=-140V; I_E=0$			-5	$\mu A$
$I_{EBO}$	Emitter cut-off current	$V_{EB}=-5V; I_C=0$			-5	$\mu A$
$h_{FE-1}$	DC current gain	$I_C=-1A; V_{CE}=-5V$	55		160	
$h_{FE-2}$	DC current gain	$I_C=-5A; V_{CE}=-5V$	35			
$f_T$	Transition frequency	$I_C=-1A; V_{CE}=-5V$		30		MHz
$C_{OB}$	Output capacitance	$I_E=0; V_{CB}=10V; f=1MHz$		320		pF

◆  $h_{FE-1}$  classifications

R	O
55-110	80-160

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PACKAGE OUTLINE

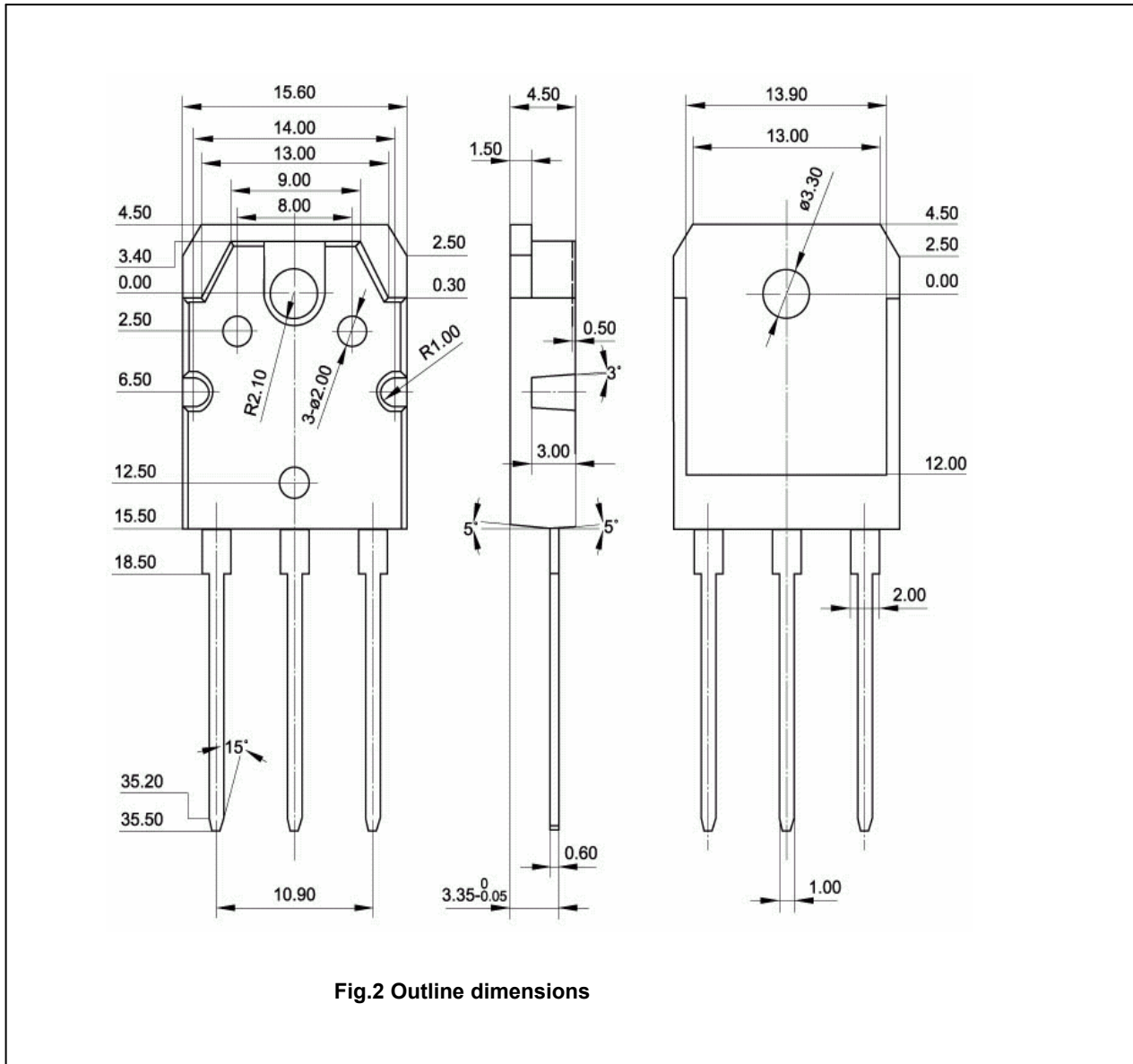


Fig.2 Outline dimensions

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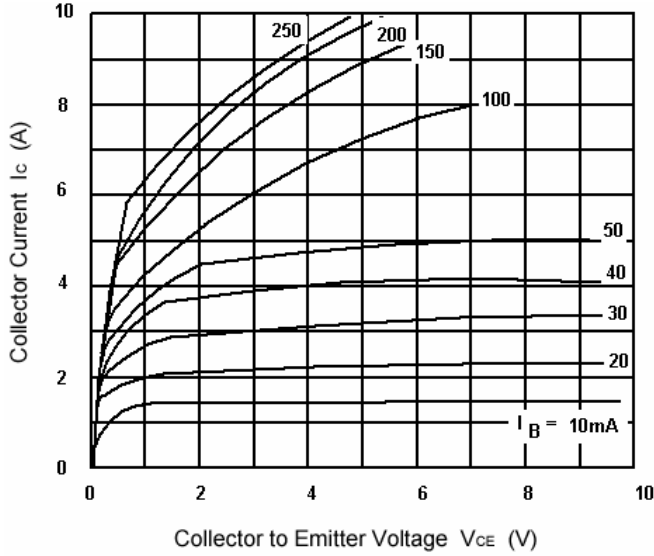


Fig.3 Static Characteristic

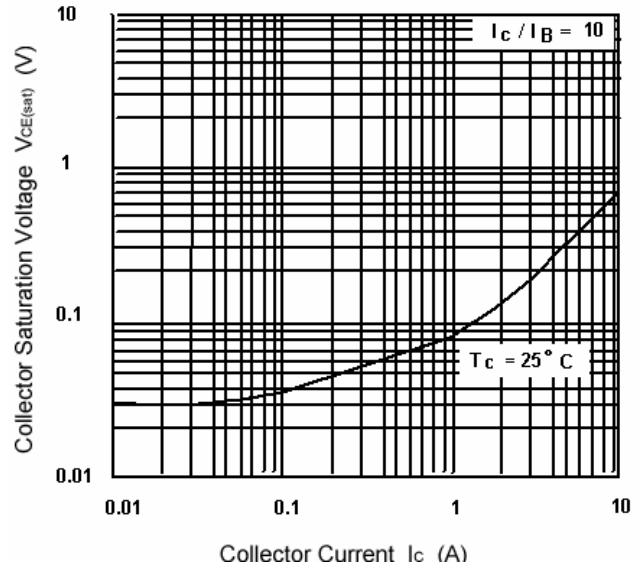


Fig.4 DC current Gain

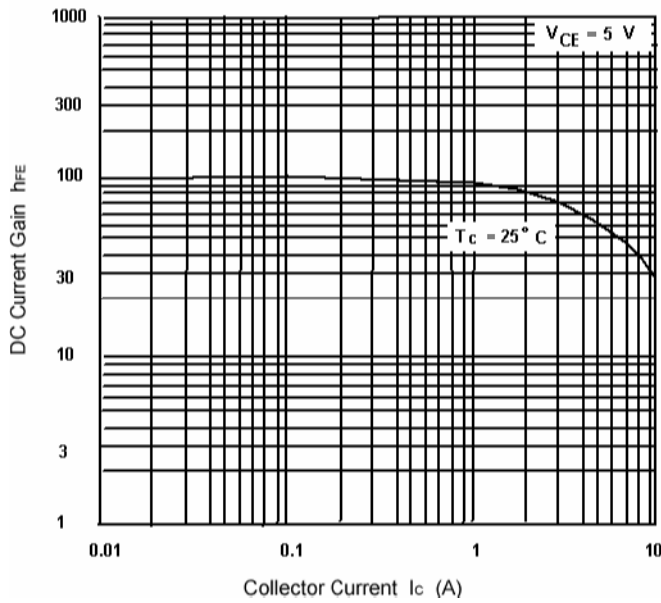


Fig.5 Collector-Emitter Saturation Voltage

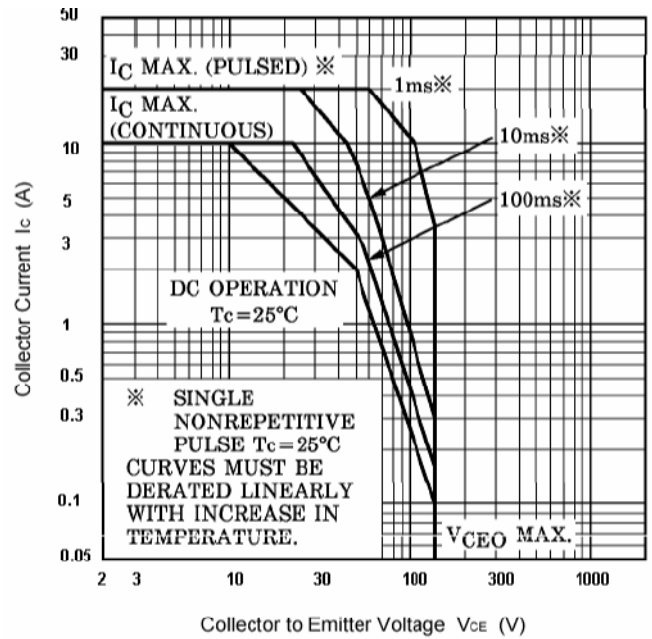


Fig.6 Safe Operating Area